TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM7785-16EL

FEATURES

- HIGH POWER
 P1dB=42.5dBm at 7.7GHz to 8.5GHz
- HIGH GAIN
 G1dB= 10.0dB at 7.7GHz to 8.5GHz
- BROAD BAND INTERNALLY MATCHED FET
- HERMETICALLY SEALED PACKAGE

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

| CHARACTERISTICS | SYMBOL | CONDITIONS | UNIT | MIN. | TYP. | MAX. |
|---------------------------|--------|----------------------------------------|------|------|------|------|
| Output Power at 1dB Gain | P1dB | | dBm | 41.5 | 42.5 | |
| Compression Point | | | | | | |
| Power Gain at 1dB Gain | G1dB | VDS= 10V | dB | 9.0 | 10.0 | _ |
| Compression Point | | IDSset=2.8A | | | | |
| Drain Current | IDS1 | f = 7.7 to 8.5GHz | Α | _ | 4.4 | 5.0 |
| Gain Flatness | ΔG | | dB | | _ | ±0.8 |
| Power Added Efficiency | ηadd | | % | _ | 36 | _ |
| 3rd Order Intermodulation | IM3 | Two-Tone Test | dBc | -40 | -45 | _ |
| Distortion | | Po= 30.5dBm | | | | |
| Drain Current | IDS2 | (Single Carrier Level) | Α | | 4.4 | 5.0 |
| Channel Temperature Rise | ΔTch | (VDS X IDS + Pin – P1dB) X Rth(c-c) | °C | | | 80 |

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

| CHARACTERISTICS | SYMBOL | CONDITIONS | UNIT | MIN. | TYP. | MAX. |
|-------------------------|----------|--------------------------|------|------|------|------|
| Transconductance | gm | VDS= 3V | S | | 5.2 | |
| | | IDS=5.2A | | | | |
| Pinch-off Voltage | VGSoff | VDS= 3V | V | -1.0 | -1.9 | -4.0 |
| | | IDS= 40mA | | | | |
| Saturated Drain Current | IDSS | VDS= 3V | Α | | 8.8 | |
| | | VGS= 0V | | | | |
| Gate-Source Breakdown | VGSO | IGS= -180 _μ A | V | -5 | | |
| Voltage | | | | | | |
| Thermal Resistance | Rth(c-c) | Channel to Case | °C/W | _ | 1.5 | 1.8 |

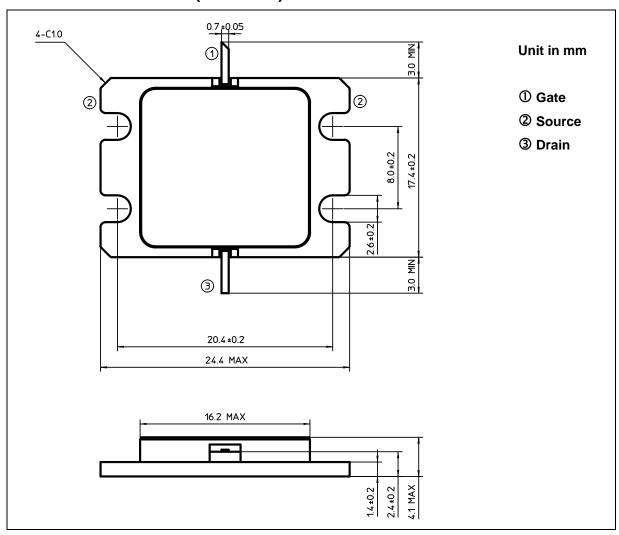
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The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

| CHARACTERISTICS | SYMBOL | UNIT | RATING |
|-------------------------------------|--------|------|-------------|
| Drain-Source Voltage | VDS | V | 15 |
| Gate-Source Voltage | VGS | V | -5 |
| Drain Current | IDS | А | 14 |
| Total Power Dissipation (Tc= 25 °C) | PT | W | 83.3 |
| Channel Temperature | Tch | °C | 175 |
| Storage | Tstg | °C | -65 to +175 |

PACKAGE OUTLINE (7-AA05A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.